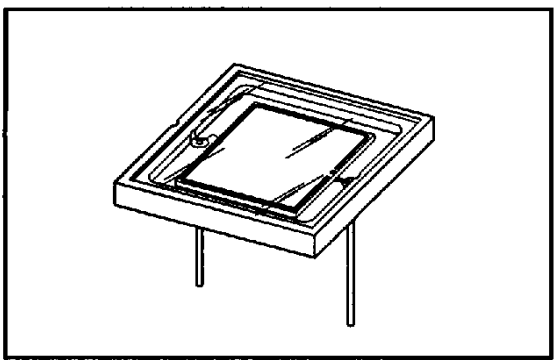




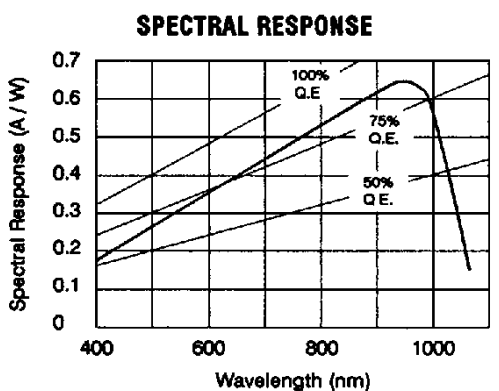
**LARGE AREA
PIN PHOTODIODE**
VTH2090, 2091
(S1723-04, 06 INDUSTRY EQUIVALENT)

E G & G VACTEC



PRODUCT DESCRIPTION

This PIN photodiode consists of a chip with a 9.2 x 9.2 mm active area mounted in a black ceramic package with an epoxy window. These devices are ideal for scintillation detection, spectrophotometry, CT scan, or other applications requiring a fast, large area, high detectivity device.



FEATURES

- High quantum efficiency
- Excellent uniformity
- High shunt impedance
- Low junction capacitance
- Fast response
- Low noise

ABSOLUTE MAXIMUM RATINGS @ 25°C UNLESS NOTED

PARAMETER	SYMBOL	RATING	UNITS
MAXIMUM CURRENT	I _{MAX}	2	mA
MAXIMUM POWER DISSIPATION	P _D	100	mW
MAXIMUM REVERSE VOLTAGE	V _{RMAX}	50	V, PEAK
TEMPERATURE RANGE			
OPERATING	T _A	- 20 to +60	°C
STORAGE	T _S	- 20 to +70	°C

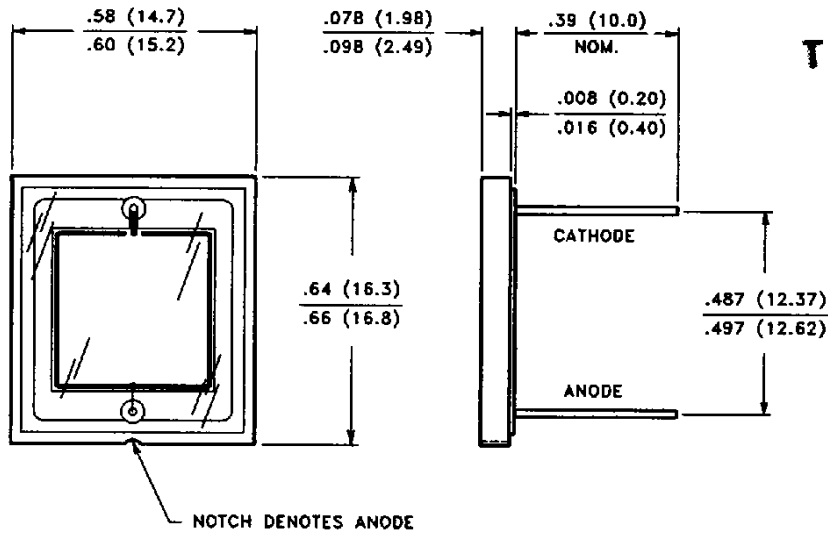
ELECTRO-OPTICAL CHARACTERISTICS @ 25° C

PART NUMBER	PEAK SPECTRAL RESPONSE λ _p , TYP. (nm)	RADIANT SENSITIVITY S _R TYP (A/W)				SHORT CIRCUIT CURRENT I _{SC} 100 LUX (μA)		DARK CURRENT I _D V _R = 30 V (nA)		TEMP. COEFF. TC, TYP. (%/°C)	JUNCTION CAPACITANCE C _J , TYP. V _R = 30 V (pF)	RISE TIME t _r TYP (ns)	NEP V _R = 30 V TYP. (W/√Hz)	D* V _R = 30 V TYP (cm√Hz/W)
		480 nm	540 nm	633 nm	940 nm	MIN.	TYP.	MAX.						
VTH2090	960	.25	.30	.40	.60	65	80	10	15		70	15	4 X 10 ⁻¹⁴	2.6 X 10 ¹³
VTH2091	960	.25	.30	.40	.60	65	80	5	15		70	15	4 X 10 ⁻¹⁴	2.6 X 10 ¹³

PACKAGE DIMENSIONS inches (mm)

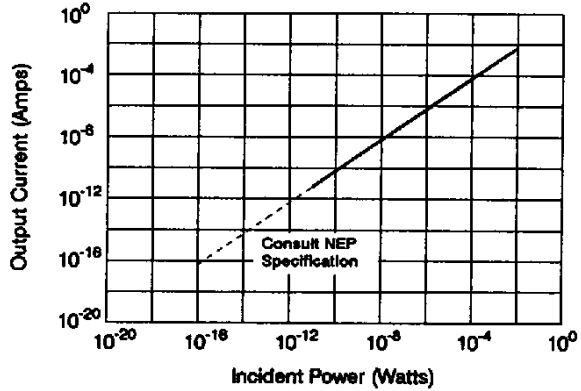
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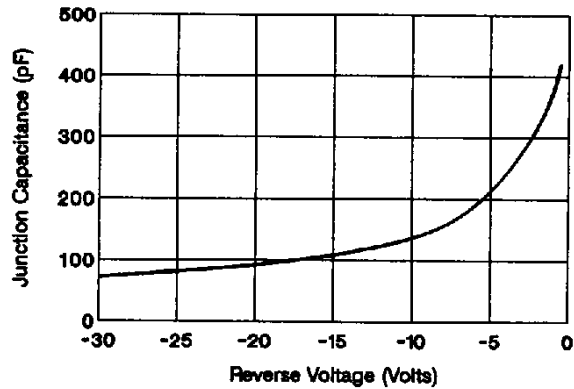


TYPICAL PERFORMANCE CURVES @ 25° C

PHOTOCURRENT LINEARITY



JUNCTION CAPACITANCE vs REVERSE VOLTAGE



Specifications subject to change without prior notice. Information supplied by EG&G Vactec is believed to be reliable, however, no responsibility is assumed for possible inaccuracies or omissions. The user should determine the suitability of this product in his own application. No patent rights are granted to any devices or circuits described herein.